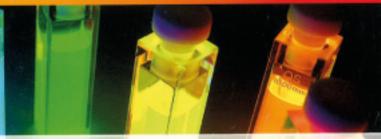
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## **BOOK OF ABSTRACTS**

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## ToF-SIMS investigations of oxygen tracer diffusion in Fe-doped SrTiO<sub>3</sub> and Sr-doped LaFeO<sub>3</sub> thin layers

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Fe-doped SrTiO<sub>3</sub> and Sr-doped LaFeO<sub>3</sub> are mixed ionic and electronic conducting perovskite oxides. SrTiO<sub>3</sub> serve as a model material for large band gap mixed conductors with well understood bulk defect chemistry while properties of thin layers are still under strong investigation [1]. The second material, LaFeO<sub>3</sub>, is a promising electrode material for solid oxide fuel cells (SOFC) in both oxidizing and reducing atmosphere [2], [3].

Accordingly, the transport and reactions kinetics of both materials are of high interest.

For this purpose thermally driven <sup>18</sup>O<sub>2</sub> isotope exchange experiments and subsequent Time-of-Flight Secondary Ion Mass Spectrometry (ToF-SIMS) analysis were performed. The diffusion profiles provide information on the tracer diffusion coefficient D\* and the surface exchange coefficient k\*.

In the case of Fe-doped SrTiO<sub>3</sub> interfacial space charge layers, which are characterized by depletion of the oxygen vacancies concentration and a spatially varying tracer diffusion coefficient, could be identified. For Sr-doped LaFeO<sub>3</sub>, a novel approach allowed comparison of k\* and D\* values under reducing and oxidizing conditions. This shows that the surface exchange reaction under oxidizing and reducing conditions is similarly fast but the diffusion coefficients differ drastically.

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